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1 Lateral dopant profiling in MOS structures on a 100 nm scale using scanning capacitance microscopy

Slinkman, J.A.; Williams, C.C.; Abraham, D.W.; Wickramasinghe, H.K.; Electron Devices Meeting, 1990. Technical Digest., International, 9-12 Dec. 1990 Pages:73 - 76

[Abstract] [PDF Full-Text (312 KB)] IEEE CNF

2 Two-dimensional dopant profiling of a 60 nm gate length nMOSFET using scanning capacitance microscopy

Timp, W.; O'Malley, M.L.; Kleiman, R.N.; Garno, J.P.;

Electron Devices Meeting, 1998. IEDM '98 Technical Digest., International, 6-9 Dec. 1998

Pages:555 - 558

[Abstract] [PDF Full-Text (976 KB)] IEEE CNF

Monitoring oxide quality using the spread of the dC/dV peak in scanning capacitance microscopy measurements

Chim, W.K.; Wong, K.M.; Yeow, Y.T.; Hong, Y.D.; Lei, Y.; Teo, L.W.; Choi, W.K.; Electron Device Letters, IEEE, Volume: 24, Issue: 10, Oct. 2003
Pages: 667 - 670

[Abstract] [PDF Full-Text (304 KB)] IEEE JNL

4 Inverse modeling of two-dimensional MOSFET dopant profile via capacitance of the source/drain gated diode

Chiang, C.Y.T.; Yeow, Y.T.;

Electron Devices, IEEE Transactions on , Volume: 47 , Issue: 7 , July 2000

Pages:1385 - 1392

[Abstract] [PDF Full-Text (280 KB)] IEEE JNL

5 Modeling study of scanning capacitance microscopy measurement for p-

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